

# Synthesis and characterization of spinel $\text{ZnAl}_2\text{O}_4\text{:SnO}_2$ thin films for optoelectronic applications

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## Introduction :

Metal oxides in thin films in general and  $\text{ZnAl}_2\text{O}_4$  films in particular have potential applications in many fields, essentially when one simulates ousley needs good transparency in the visible and good electrical conductivity [1-3]. Zinc aluminate ( $\text{ZnAl}_2\text{O}_4$ ) whose natural mineral called gahnite is a spinel oxide with cubic structure (space group Fd-3m) [1-2]. It has several advantages, such as high chemical and thermal stability, good catalytic activity, low-temperature sinter ability, and mechanical strength. In addition, it is classified as a transparent wide-bandgap semiconductor with estimated gap energy of 3.8 eV. Due to its characteristics,  $\text{ZnAl}_2\text{O}_4$  is important in many technological applications such as catalysis, ceramics, aerospace, dielectrics, electronics, and optoelectronic devices [3-4]. It has been reported that the addition of metallic impurities, in the form of atoms or oxides to  $\text{ZnAl}_2\text{O}_4$  adjusts both the crystallite size and the bandgap, resulting in an improvement in many properties and consequently offering greater application potential [5-7]. In this work, sol-gel process was chosen to produce the  $\text{ZnAl}_2\text{O}_4$  films. It makes it possible to obtain a material of high purity having good homogeneity compared to other conventional production methods such as chemical vapor deposition, pyrolysis or spraying. X-ray powder diffractograms of pure Gahnite.

## Results :

Our study highlights the following results: All diffractograms consist of a single crystalline phase with a cubic spinel structure, and they showed a preferred orientation along the (220) axis with a decrease in grain size from 32.45 nm for undoped  $\text{ZnAl}_2\text{O}_4$  to 17.18 nm for  $\text{ZnAl}_2\text{O}_4$  doped with 6%  $\text{SnO}_2$ . The roughness parameter reveals a decrease with thickness. The AFM studies

revealed uniform surface and the effect of doping on the roughness of the layers has also been highlighted. We tracked the evolution of the surface roughness of the films as a function of the tin oxide content. This is due to the coalescence of grains resulting at the annealing temperature and the effect of SnO<sub>2</sub> on the ZnAl<sub>2</sub>O<sub>4</sub> matrix. The UV-Visible spectra show a high transmittance in the visible light range ( $T \sim 98\%$  for pure ZnAl<sub>2</sub>O<sub>4</sub> and between 85% and 86% for all doped samples). The optical gap varies from 3.80 eV (for the undoped) to 3.68 eV for the sample doped with 6% SnO<sub>2</sub>. The infrared transmission spectra obtained for different tin dioxide doping levels show a band observed at 3599 cm<sup>-1</sup>, which can be attributed to the stretching vibration of H<sub>2</sub>O molecules. The bands at 655 cm<sup>-1</sup> confirm the formation of the normal spinel structure, ZnAl<sub>2</sub>O<sub>4</sub>. Complex impedance spectroscopy indicates that the effect of grain boundaries is dominant in the conduction mechanism. It is also observed that the equivalent circuit of undoped and SnO<sub>2</sub>-doped ZnAl<sub>2</sub>O<sub>4</sub> films is a parallel RC circuit.

## Conclusion :

Based on these results, we conclude that SnO<sub>2</sub> doping allows obtaining ZnAl<sub>2</sub>O<sub>4</sub> thin films with very interesting structural and optical properties, making these films a good alternative for optoelectronic applications, such as LEDs and lasers.

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